

# EVVOSEMI<sup>®</sup>

THINK CHANGE DO



ESD



TVS



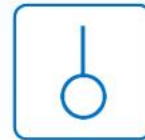
MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

▶ Domestic	Part Number	MB1S - MB10S
▶ Overseas	Part Number	MB1S - MB10S
▶ Equivalent	Part Number	MB1S - MB10S

EV is the abbreviation of name EVVO

## ■ 1A Surface Mount Glass Passivated Bridge Rectifier

### ■ Features

- Glass Passivated Chip Junction
- Reverse Voltage - 100 to 1000 V
- Forward Current - 1 A
- High Surge Current Capability
- Designed for Surface Mount Application



■ Simplified outline(MBS)

### Pinning

PIN	DESCRIPTION
1	Input Pin ( ~ )
2	Input Pin ( ~ )
3	Output Anode ( + )
4	Output Cathode ( - )

### ■ Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

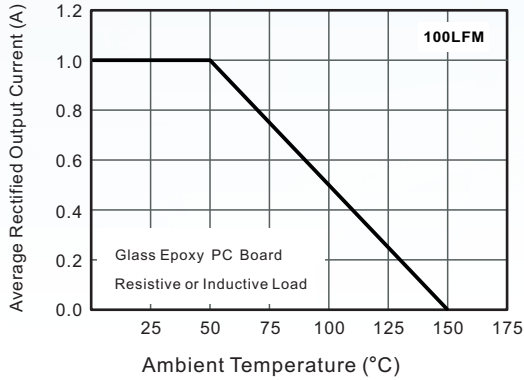
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	MB1S	MB2S	MB4S	MB6S	MB8S	MB10S	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	100	200	400	600	800	1000	V
Average Rectified Output Current at $T_a = 50\text{ }^\circ\text{C}$	$I_O$	1.0						A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	$I_{FSM}$	35						A
Maximum Forward Voltage at 1.0 A	$V_F$	1.1						V
Maximum DC Reverse Current at Rated DC Blocking Voltage	$I_R$	@ $T_a=25\text{ }^\circ\text{C}$ 5						$\mu\text{A}$
		@ $T_a=125\text{ }^\circ\text{C}$ 40						
Typical Junction Capacitance ( Note1 )	$C_j$	13						pF
Typical Thermal Resistance ( Note2 )	$R_{\theta JA}$ $R_{\theta JL}$	85						$^\circ\text{C/W}$
		30						
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150						$^\circ\text{C}$

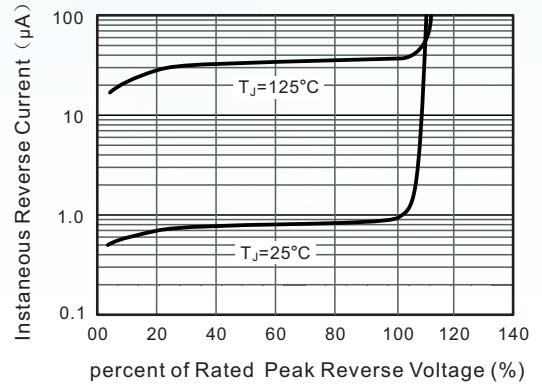
Note: 1. Measured at 1MHz and applied reverse voltage of 4 V D.C.

2. Mounted on glass epoxy PC board with  $4 \times (5 \times 5\text{mm}^2)$  copper pad.

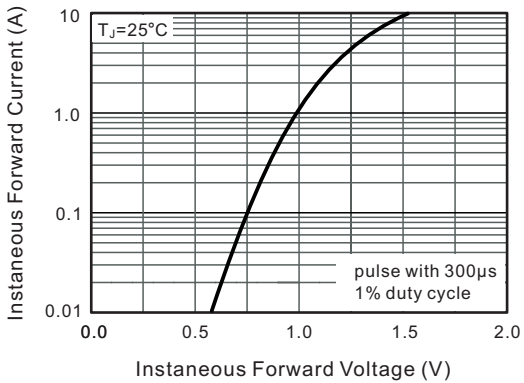
**Fig.1 Average Rectified Output Current Derating Curve**



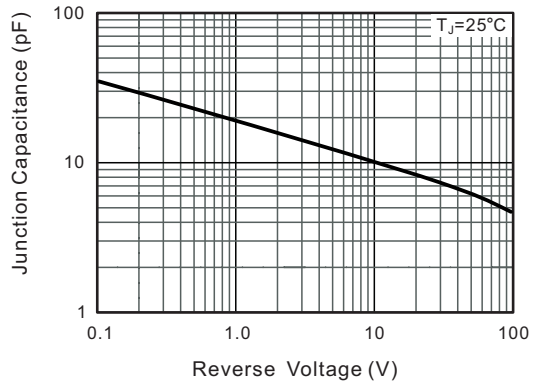
**Fig.2 Typical Reverse Characteristics**



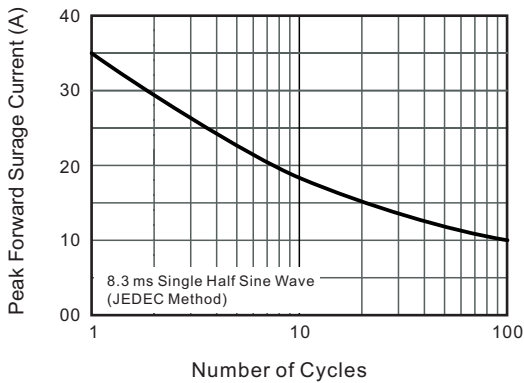
**Fig.3 Typical Instantaneous Forward Characteristics**



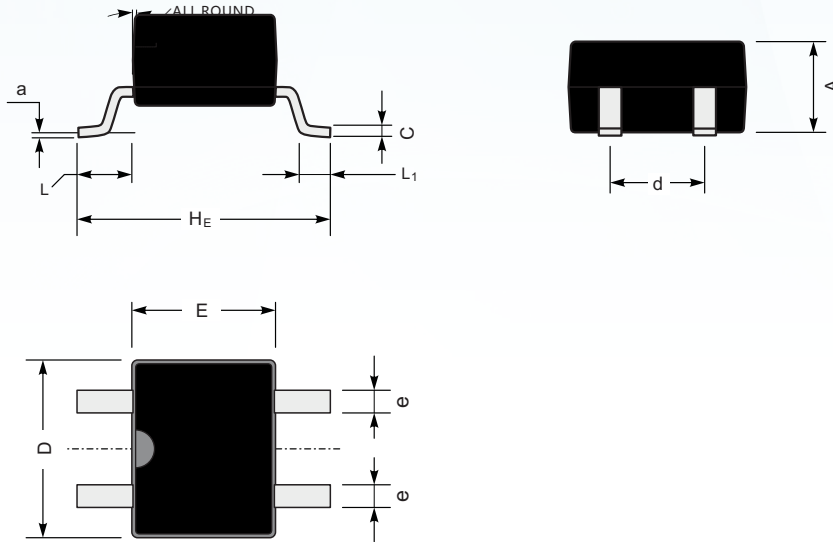
**Fig.4 Typical Junction Capacitance**



**Fig.5 Maximum Non-Repetitive Peak Forward Surge Current**



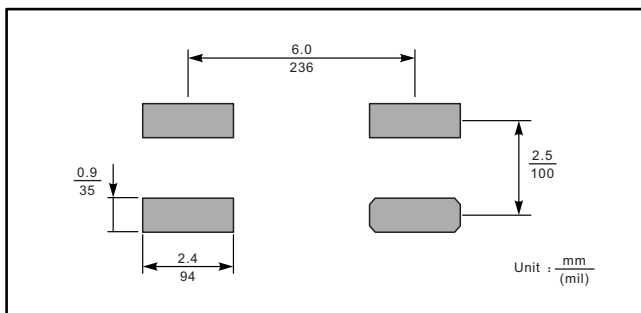
■ MBS



MBS mechanical data

UNIT		A	C	D	E	H <sub>E</sub>	d	e	L	L <sub>1</sub>	a	∠
mm	max	2.6	0.22	5.0	4.1	7.0	2.7	0.7	1.7	1.1	0.2	7°
	min	2.2	0.15	4.5	3.6	6.4	2.3	0.5	1.3	0.5	—	
mil	max	102	8.7	197	161	276	106	28	67	43	8	
	min	94	5.9	177	142	252	91	20	51	20	—	

The recommended mounting pad size



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